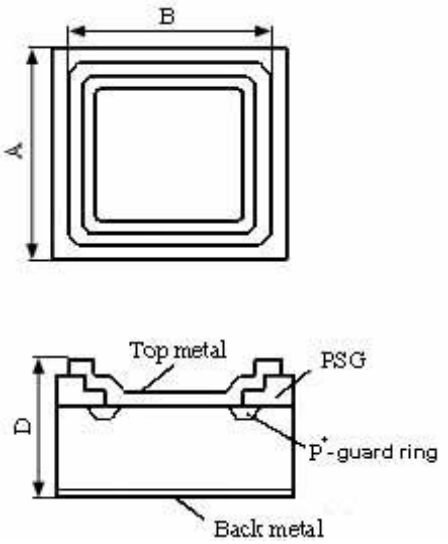
mikron VSP-MIKRON

	15A/45V. Die Size-130mil. RoHS			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	45	50
Average Rectified Forward Current	$I_{F(AV)}$	A	15,0	-
DC Forward Voltage @ 25˚C, I_F=15,0A	V_F	V	0,50	0,48
Maximum Reverse Current @ 25˚C, V_R=50V @ 25˚C, V_R=45V @ 125˚C, V_R=45V	I_R	mA	- 0,200 120,0	0,200 0,150 100,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	300	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<150˚C.	I_{RRM}	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	150	



DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	3300 3300
B_X B_y	Top Metal Size	3160 3160
D	Thickness	300max.
Scribe line Width		80

Top metal:
a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.